

7. SILICON FIELD EFFECT TRANSISTORS - N CHANNEL

IN ORDER OF (1) DISSIPATION (2) TYPE No.

Table with columns: LINE No., TYPE No., MAX. DEVICE DISS @ 25°C (W), MAX. Vp (V), ABS MAX RATINGS @ 25°C (BVdss, BVgss, Id, Ig, Vgss @ Id, Vgs @ Id, Vgs @ Vds), TEST COND (Vgs, Vds), COMMON SOURCE PARAMETERS @ 25°C (MIN, MAX, mhos, Yos), r(DS) on, MAX. Cis, IN FREE AIR W/C, MAX TEMP (°C), STRUCTURE, DWG Y200 s/a TO200 Ser, # OF PINS, EOD, C, A, D, E